

# IRF7904TRPBF Datasheet



DiGi Electronics Part Number	IRF7904TRPBF-DG
Manufacturer	<a href="#">Infineon Technologies</a>
Manufacturer Product Number	IRF7904TRPBF
Description	MOSFET 2N-CH 30V 7.6A/11A 850
Detailed Description	Mosfet Array 30V 7.6A, 11A 1.4W, 2W Surface Mount 8-SO

<https://www.DiGi-Electronics.com>



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## Purchase and inquiry

Manufacturer Product Number:

IRF7904TRPBF

Series:

HEXFET®

Technology:

MOSFET (Metal Oxide)

FET Feature:

Logic Level Gate

Current - Continuous Drain (Id) @ 25°C:

7.6A, 11A

Vgs(th) (Max) @ Id:

2.25V @ 25µA

Input Capacitance (Ciss) (Max) @ Vds:

910pF @ 15V

Operating Temperature:

-55°C ~ 150°C (Tj)

Package / Case:

8-SOIC (0.154", 3.90mm Width)

Base Product Number:

IRF7904

Manufacturer:

Infineon Technologies

Product Status:

Not For New Designs

Configuration:

2 N-Channel (Half Bridge)

Drain to Source Voltage (Vdss):

30V

Rds On (Max) @ Id, Vgs:

16.2mOhm @ 7.6A, 10V

Gate Charge (Qg) (Max) @ Vgs:

11nC @ 4.5V

Power - Max:

1.4W, 2W

Mounting Type:

Surface Mount

Supplier Device Package:

8-SO

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



HEXFET® Power MOSFET

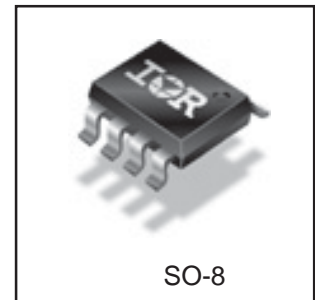
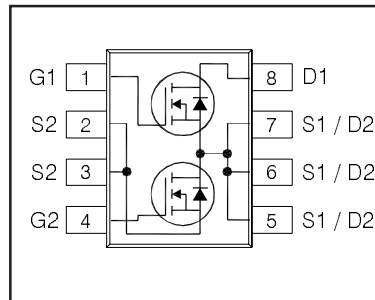
**Applications**

- Dual SO-8 MOSFET for POL Converters in Notebook Computers, Servers, Graphics Cards, Game Consoles and Set-Top Box

$V_{DSS}$	$R_{DS(on)}$ max	$I_D$
<b>30V</b>	<b>Q1</b> 16.2m $\Omega$ @ $V_{GS} = 10V$	<b>7.6A</b>
	<b>Q2</b> 10.8m $\Omega$ @ $V_{GS} = 10V$	<b>11A</b>

**Benefits**

- Very Low  $R_{DS(on)}$  at 4.5V  $V_{GS}$
- Low Gate Charge
- Fully Characterized Avalanche Voltage and Current
- 20V  $V_{GS}$  Max. Gate Rating
- Improved Body Diode Reverse Recovery
- 100% Tested for  $R_G$
- Lead-Free

**Absolute Maximum Ratings**

	Parameter	Q1 Max.	Q2 Max.	Units
$V_{DS}$	Drain-to-Source Voltage	30		V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$		
$I_D$ @ $T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	7.6	11	A
$I_D$ @ $T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	6.1	8.9	
$I_{DM}$	Pulsed Drain Current ①	61	89	
$P_D$ @ $T_A = 25^\circ\text{C}$	Power Dissipation	1.4	2.0	W
$P_D$ @ $T_A = 70^\circ\text{C}$	Power Dissipation	0.9	1.3	
	Linear Derating Factor	0.011	0.016	W/ $^\circ\text{C}$
$T_J$	Operating Junction and	-55 to + 150		$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range			

**Thermal Resistance**

	Parameter	Q1 Max.	Q2 Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead ⑤	20	20	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-Ambient ④⑤	90	62.5	

## IRF7904PbF

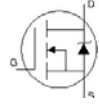
International  
IR RectifierStatic @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter		Min.	Typ.	Max.	Units	Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	Q1&Q2	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	Q1	—	0.024	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
		Q2	—	0.024	—		
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	Q1	—	11.4	16.2	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 7.6A ③
			—	14.5	20.5		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 6.1A ③
		Q2	—	8.6	10.8		V <sub>GS</sub> = 10V, I <sub>D</sub> = 11A ③
			—	10	13		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 8.8A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	Q1&Q2	1.35	—	2.25	V	Q1: V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 25μA Q2: V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 50μA
ΔV <sub>GS(th)</sub> /ΔT <sub>J</sub>	Gate Threshold Voltage Coefficient	Q1	—	-5.0	—	mV/°C	
		Q2	—	-5.0	—		
I <sub>DSS</sub>	Drain-to-Source Leakage Current	Q1&Q2	—	—	1.0	μA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
		Q1&Q2	—	—	150		V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	Q1&Q2	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	Q1&Q2	—	—	-100		V <sub>GS</sub> = -20V
g <sub>fs</sub>	Forward Transconductance	Q1	17	—	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 6.1A
		Q2	23	—	—		V <sub>DS</sub> = 15V, I <sub>D</sub> = 8.8A
Q <sub>g</sub>	Total Gate Charge	Q1	—	7.5	11	nC	Q1 V <sub>DS</sub> = 15V V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 6.1A  Q2 V <sub>DS</sub> = 15V V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 8.8A
Q <sub>gs1</sub>	Pre-V <sub>th</sub> Gate-to-Source Charge	Q1	—	2.2	—		
		Q2	—	3.7	—		
Q <sub>gs2</sub>	Post-V <sub>th</sub> Gate-to-Source Charge	Q1	—	0.6	—		
		Q2	—	1.1	—		
Q <sub>gd</sub>	Gate-to-Drain Charge	Q1	—	2.5	—		
		Q2	—	4.8	—		
Q <sub>qodr</sub>	Gate Charge Overdrive	Q1	—	2.2	—		
		Q2	—	4.4	—		
Q <sub>sw</sub>	Switch Charge (Q <sub>gs2</sub> + Q <sub>gd</sub> )	Q1	—	3.1	—		
		Q2	—	5.9	—		
Q <sub>oss</sub>	Output Charge	Q1	—	4.5	—	nC	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
		Q2	—	9.1	—		
R <sub>G</sub>	Gate Resistance	Q1	—	3.2	4.8	Ω	
		Q2	—	2.9	4.4		
t <sub>d(on)</sub>	Turn-On Delay Time	Q1	—	6.9	—	ns	Q1 V <sub>DD</sub> = 15V, V <sub>GS</sub> = 4.5V I <sub>D</sub> = 6.1A  Q2 V <sub>DD</sub> = 15V, V <sub>GS</sub> = 4.5V I <sub>D</sub> = 8.8A Clamped Inductive Load
		Q2	—	7.8	—		
t <sub>r</sub>	Rise Time	Q1	—	7.3	—		
		Q2	—	10	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	Q1	—	10	—		
		Q2	—	15	—		
t <sub>f</sub>	Fall Time	Q1	—	3.2	—		
		Q2	—	4.6	—		
C <sub>iss</sub>	Input Capacitance	Q1	—	910	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = 15V f = 1.0MHz
		Q2	—	1780	—		
C <sub>oss</sub>	Output Capacitance	Q1	—	190	—		
		Q2	—	390	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	Q1	—	94	—		
		Q2	—	180	—		

## Avalanche Characteristics

	Parameter	Typ.	Q1 Max.	Q2 Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy ②	—	140	250	mJ
I <sub>AR</sub>	Avalanche Current ①	—	6.1	8.8	A

## Diode Characteristics

	Parameter		Min.	Typ.	Max.	Units	Conditions	
I <sub>S</sub>	Continuous Source Current (Body Diode)	Q1	—	—	1.8	A	MOSFET symbol showing the integral reverse p-n junction diode. 	
		Q2	—	—	2.5			
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	Q1	—	—	61	A		
		Q2	—	—	88			
V <sub>SD</sub>	Diode Forward Voltage	Q1	—	—	1.0	V		T <sub>J</sub> = 25°C, I <sub>S</sub> = 6.1A, V <sub>GS</sub> = 0V ③
		Q2	—	—	1.0			T <sub>J</sub> = 25°C, I <sub>S</sub> = 8.8A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	Q1	—	11	17	ns		Q1 T <sub>J</sub> = 25°C, I <sub>F</sub> = 6.1A, V <sub>DD</sub> = 15V, di/dt = 100A/μs ③
		Q2	—	16	24			
Q <sub>rr</sub>	Reverse Recovery Charge	Q1	—	2.6	3.9	nC	Q2 T <sub>J</sub> = 25°C, I <sub>F</sub> = 8.8A, V <sub>DD</sub> = 15V, di/dt = 100A/μs ③	
		Q2	—	6.9	10			

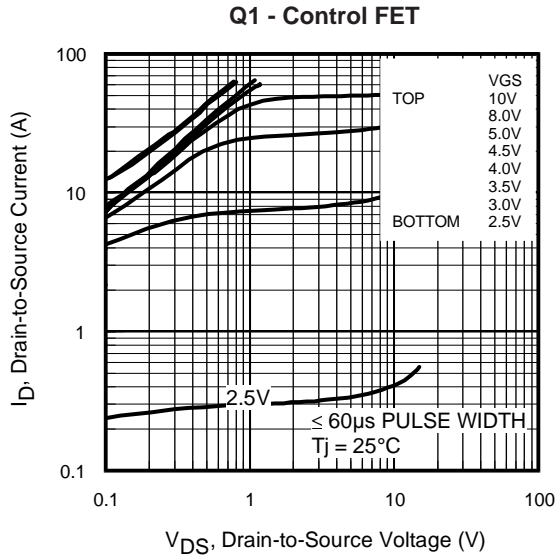


Fig 1. Typical Output Characteristics

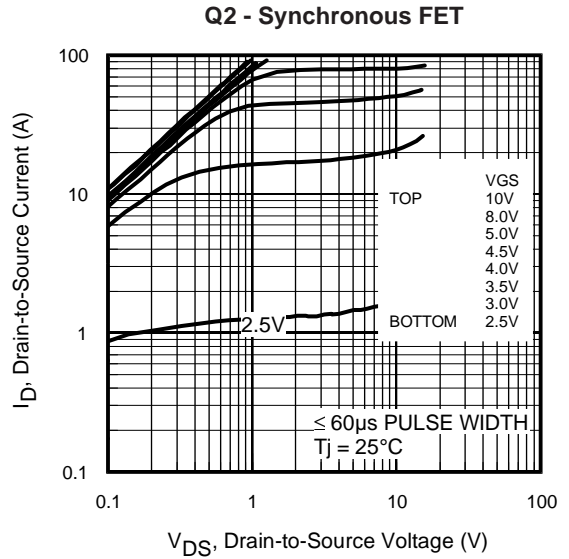


Fig 2. Typical Output Characteristics

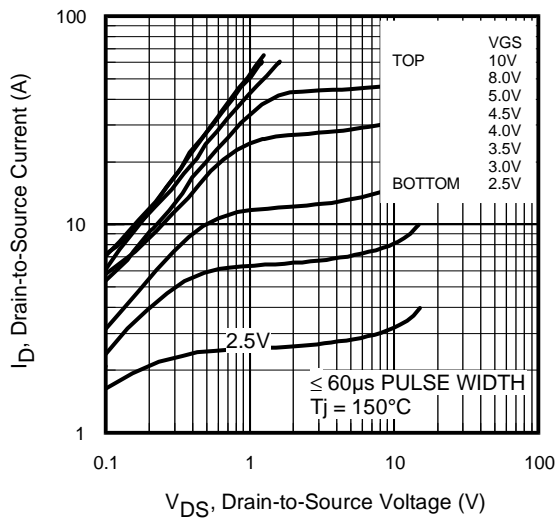


Fig 3. Typical Output Characteristics

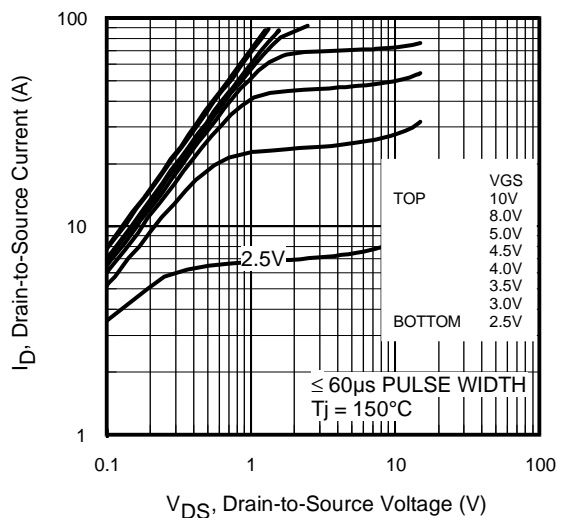


Fig 4. Typical Output Characteristics

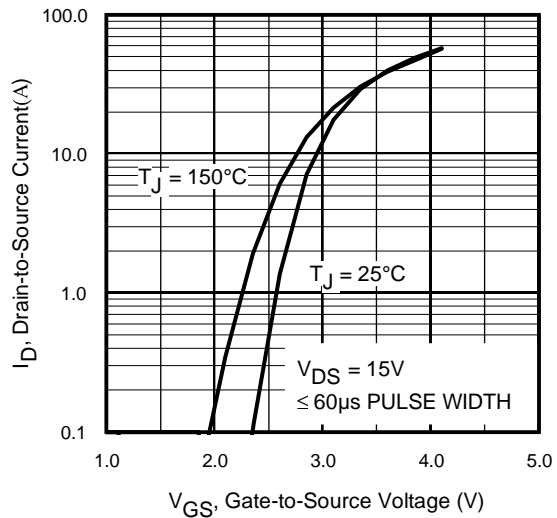


Fig 5. Typical Transfer Characteristics

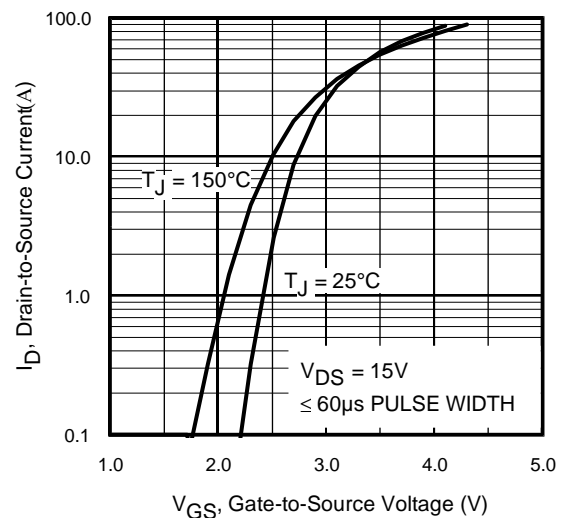


Fig 6. Typical Transfer Characteristics

# IRF7904PbF

## Typical Characteristics

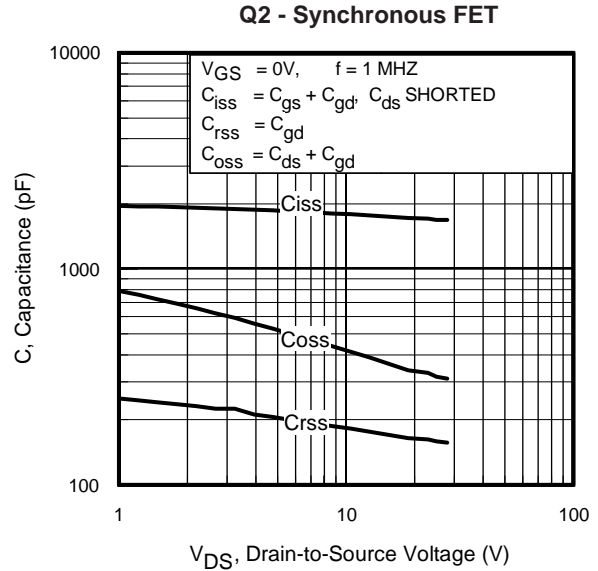
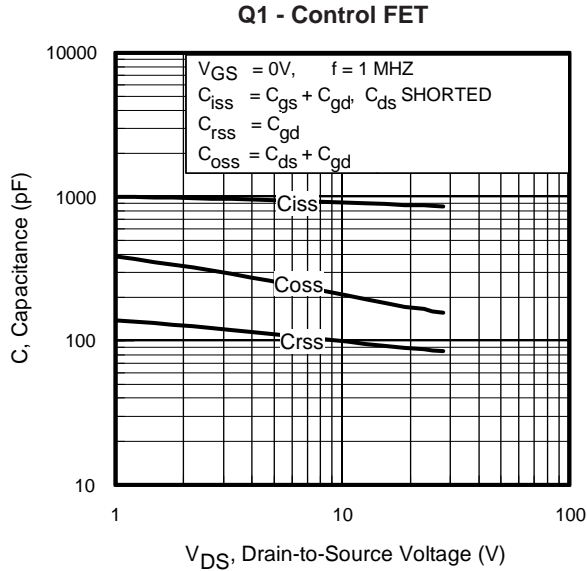


Fig 7. Typical Capacitance vs. Drain-to-Source Voltage

Fig 8. Typical Capacitance vs. Drain-to-Source Voltage

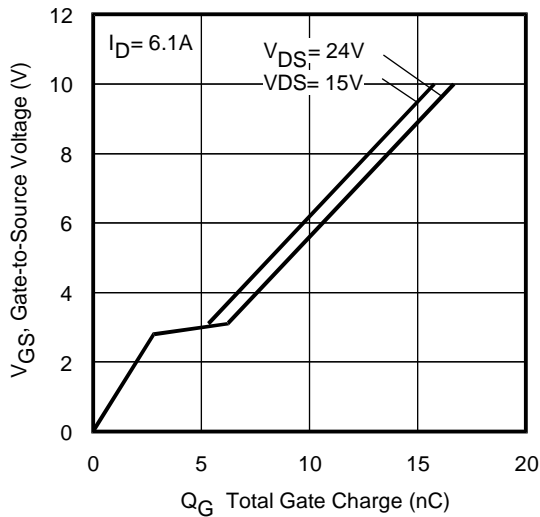


Fig 9. Typical Gate Charge vs. Gate-to-Source Voltage

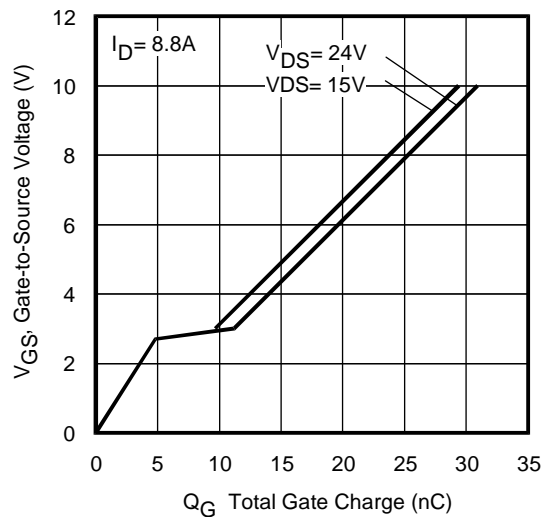


Fig 10. Typical Gate Charge vs. Gate-to-Source Voltage

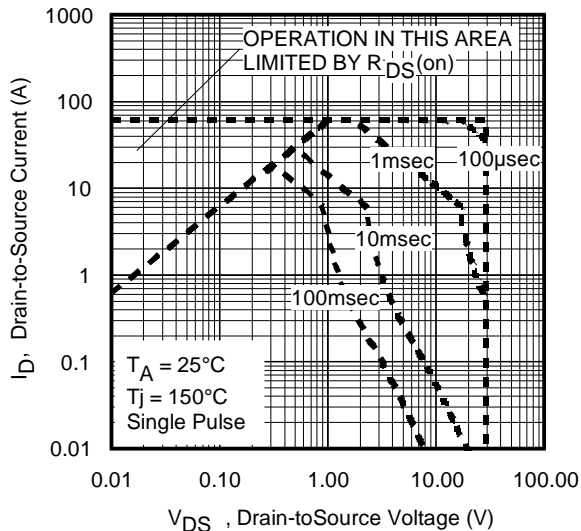


Fig 11. Maximum Safe Operating Area

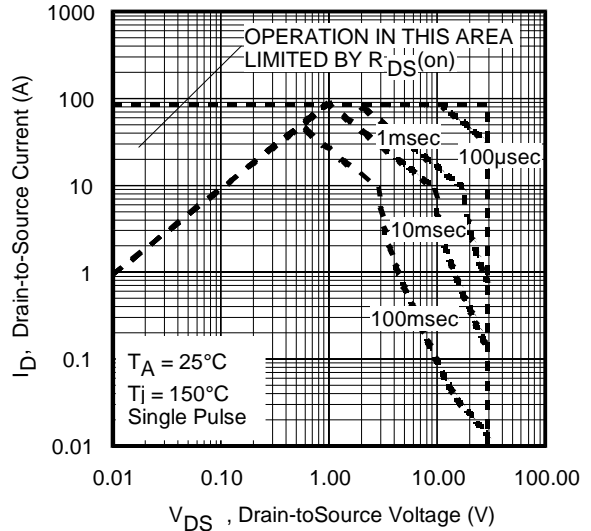


Fig 12. Maximum Safe Operating Area

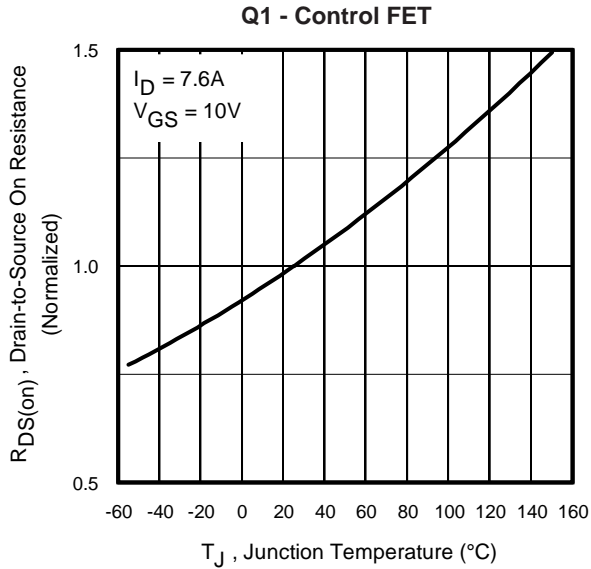


Fig 13. Normalized On-Resistance vs. Temperature

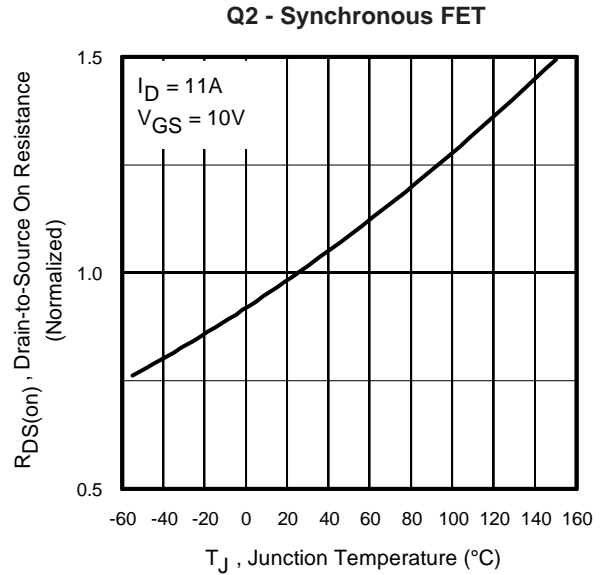


Fig 14. Normalized On-Resistance vs. Temperature

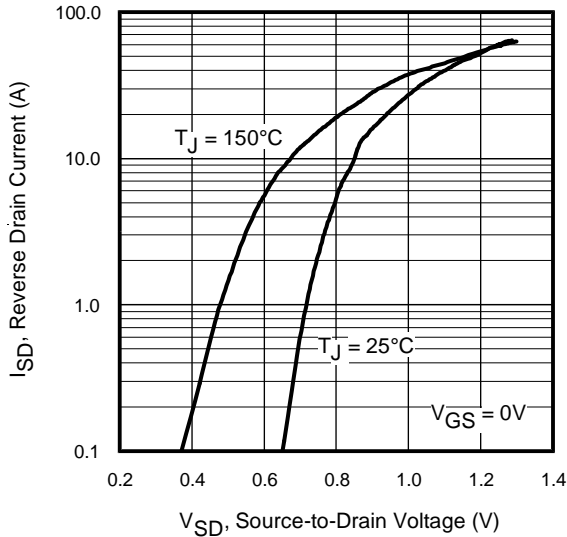


Fig 15. Typical Source-Drain Diode Forward Voltage

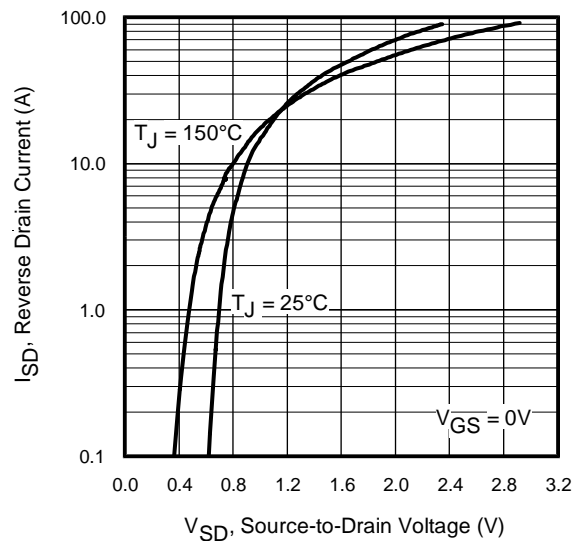


Fig 16. Typical Source-Drain Diode Forward Voltage

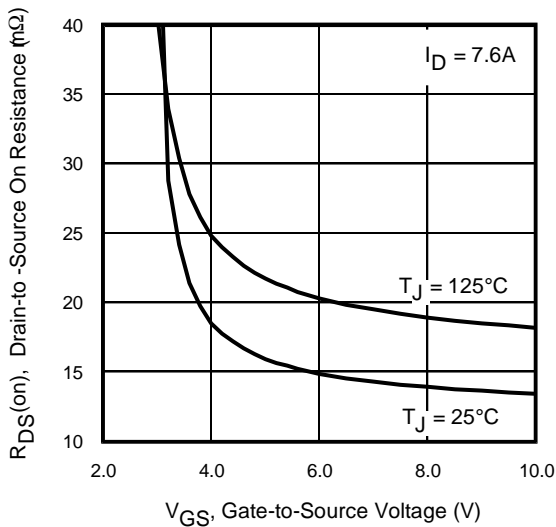


Fig 17. Typical On-Resistance vs. Gate Voltage

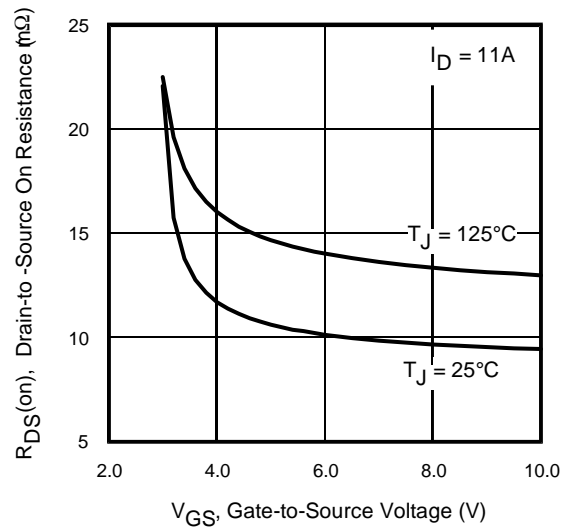
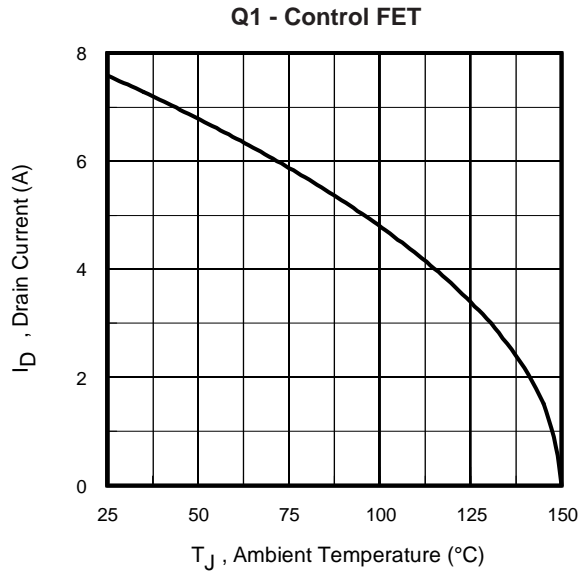


Fig 18. Typical On-Resistance vs. Gate Voltage

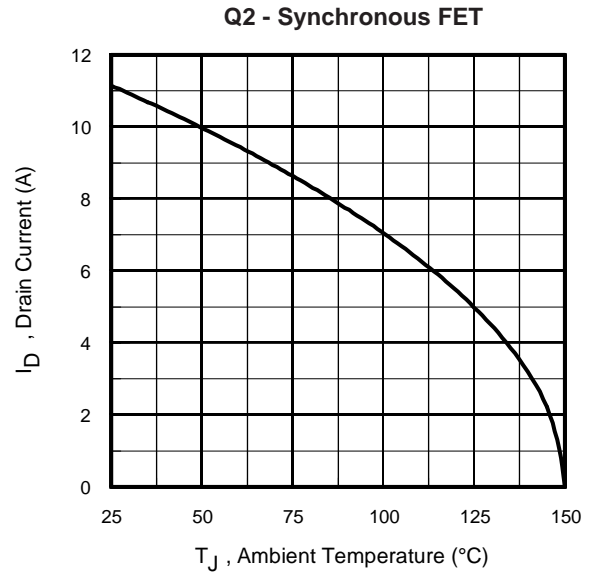
# IRF7904PbF

## Typical Characteristics

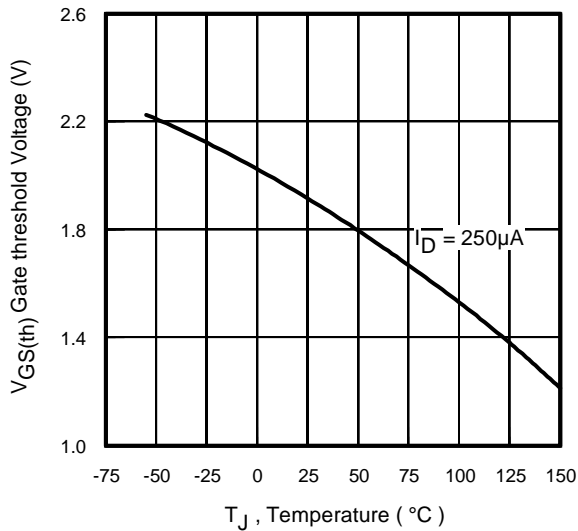
International  
**IGOR** Rectifier



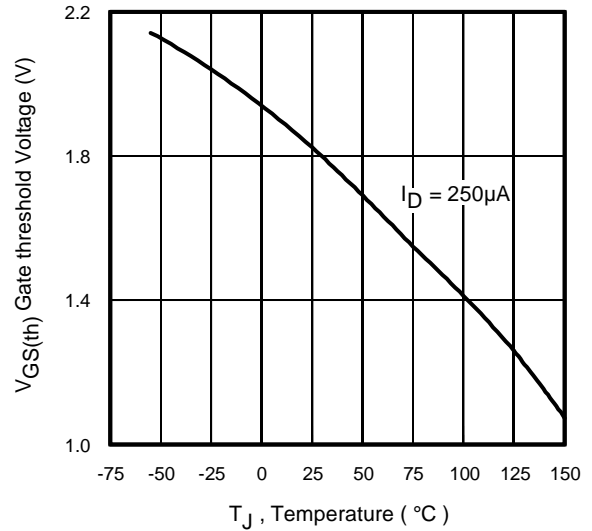
**Fig 19.** Maximum Drain Current vs. Ambient Temp.



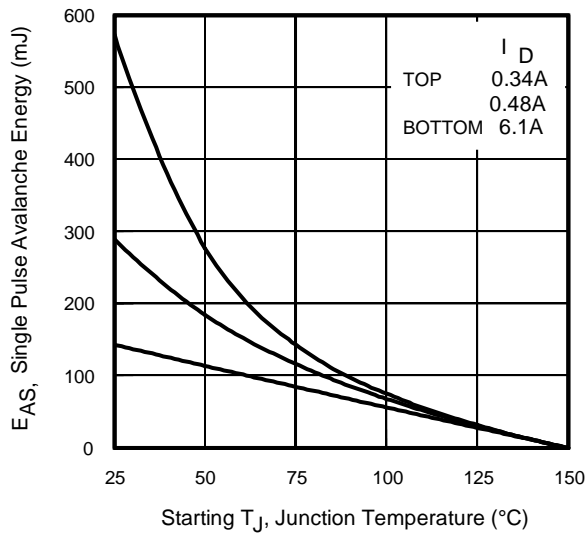
**Fig 20.** Maximum Drain Current vs. Ambient Temp.



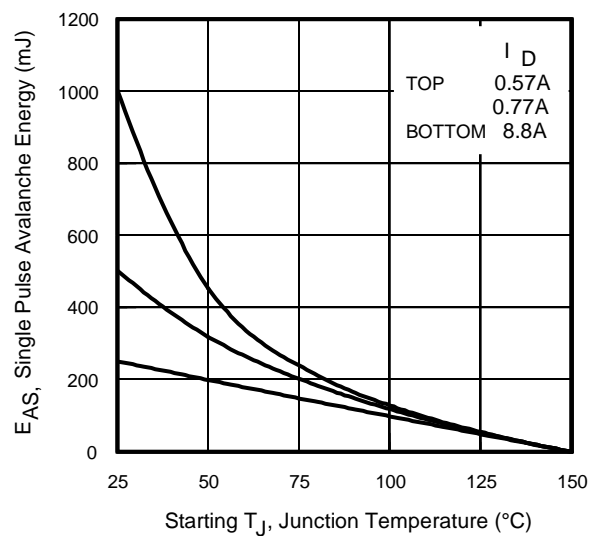
**Fig 21.** Threshold Voltage vs. Temperature



**Fig 22.** Threshold Voltage vs. Temperature



**Fig 23.** Maximum Avalanche Energy vs. Drain Current



**Fig 24.** Maximum Avalanche Energy vs. Drain Current



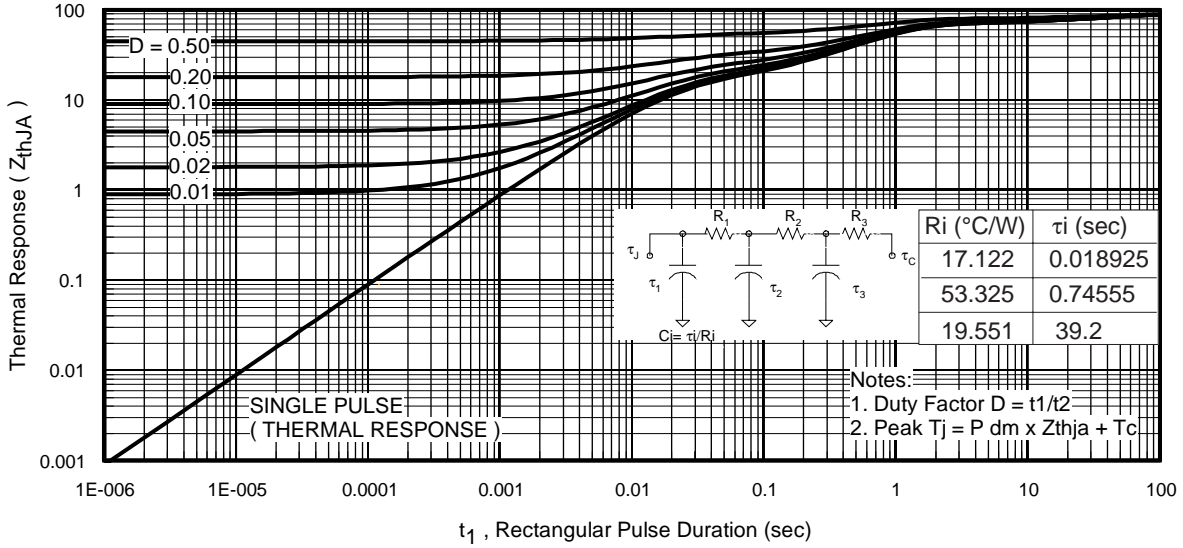


Fig 25. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient (Q1)

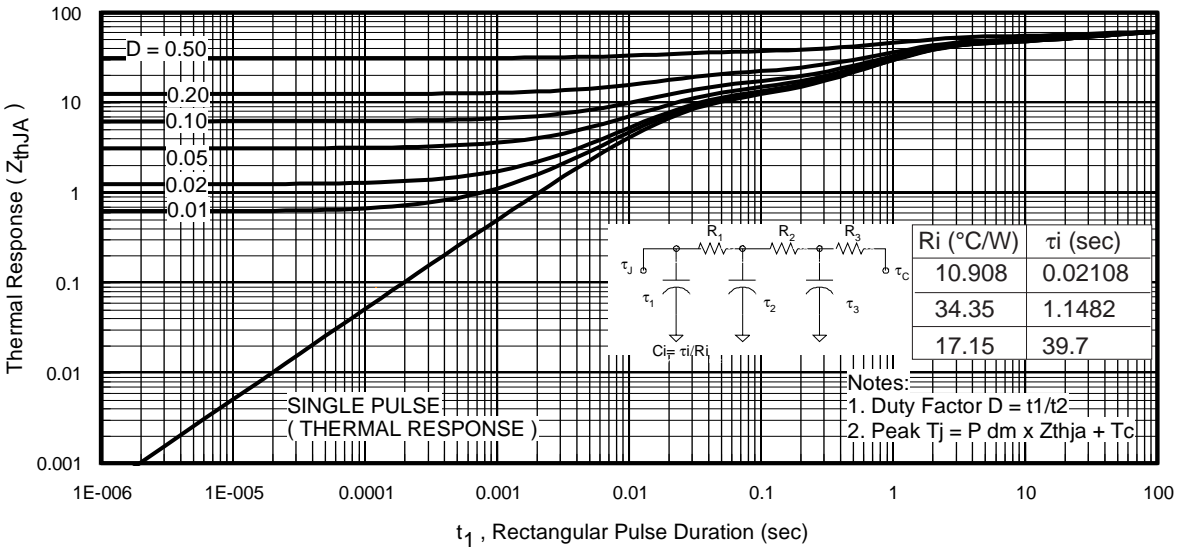


Fig 26. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient (Q2)

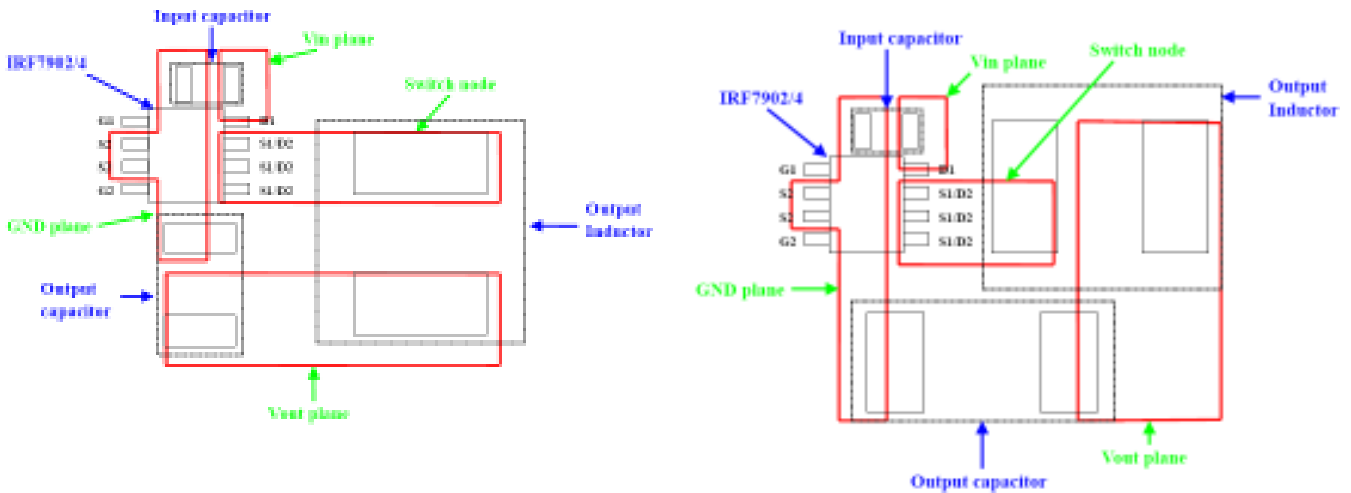
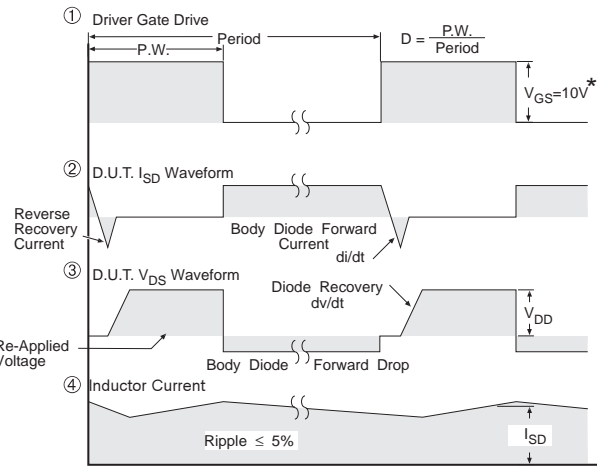
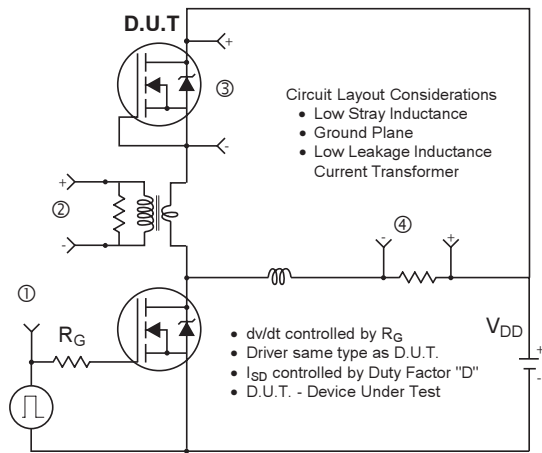


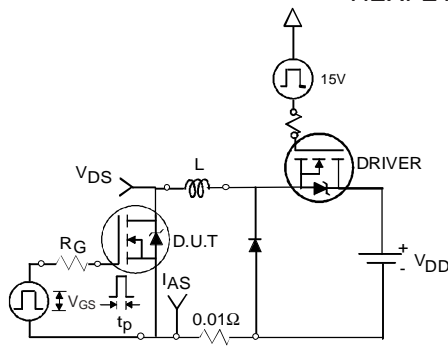
Fig 27. Layout Diagram

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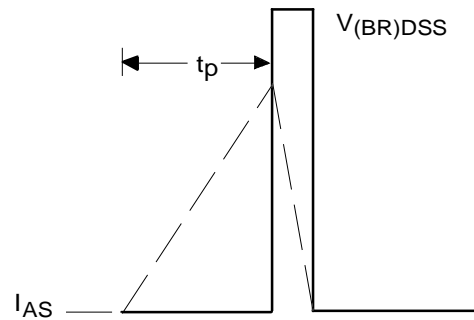


\*  $V_{GS} = 5V$  for Logic Level Devices

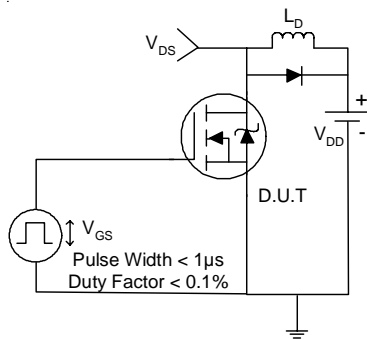
**Fig 28. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs**



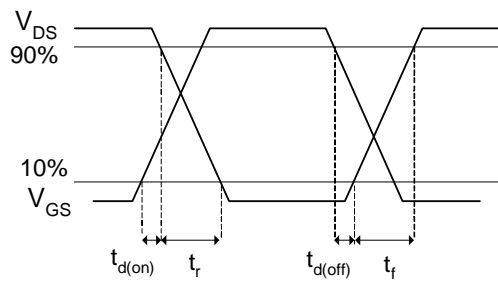
**Fig 29a. Unclamped Inductive Test Circuit**



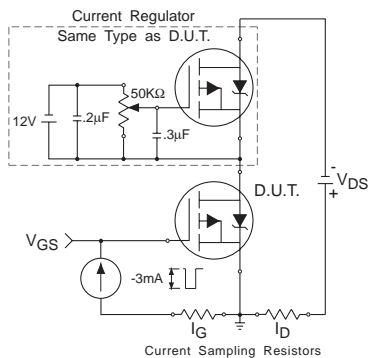
**Fig 29b. Unclamped Inductive Waveforms**



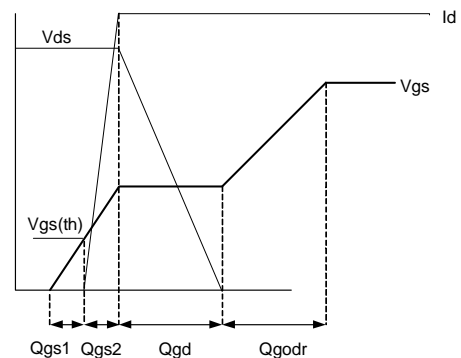
**Fig 30a. Switching Time Test Circuit**



**Fig 30b. Switching Time Waveforms**



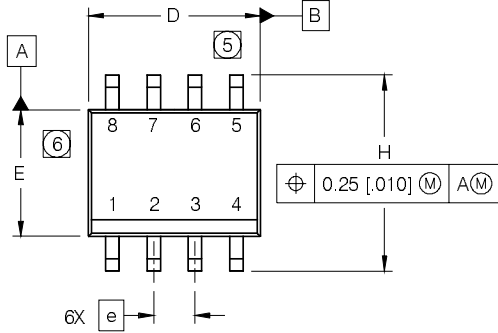
**Fig 31a. Gate Charge Test Circuit**



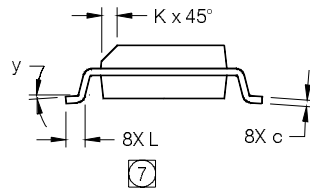
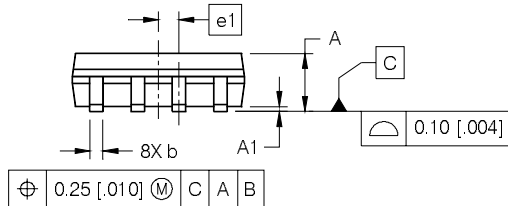
**Fig 31b. Gate Charge Waveform**

SO-8 Package Outline

Dimensions are shown in millimeters (inches)



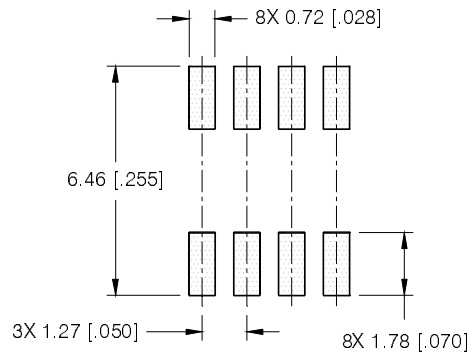
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



NOTES:

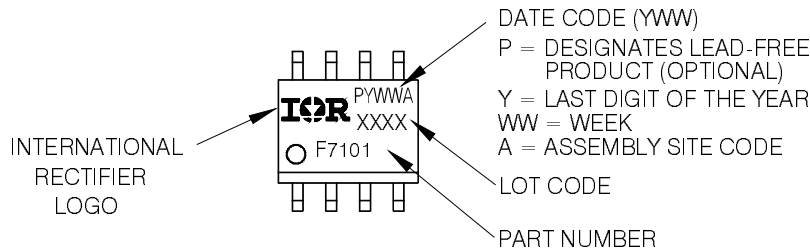
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



SO-8 Part Marking

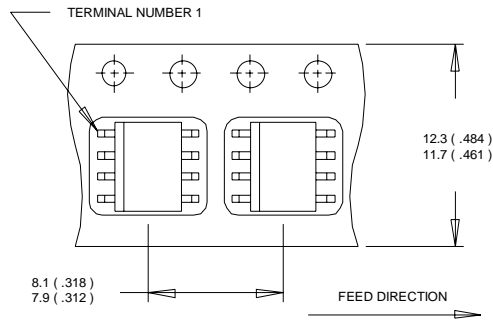
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



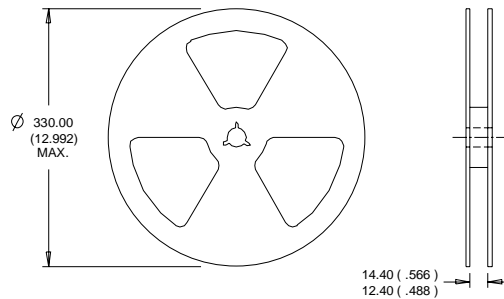
# IRF7904PbF

## SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ , Q1:  $L = 7.7\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 6.1\text{A}$ ; Q2:  $L = 6.5\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 8.8\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ When mounted on 1 inch square copper board.
- ⑤  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Consumer market.  
Qualification Standards can be found on IR's Web site.



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